

9. (Amended) A method of fabricating a liquid crystal display device, comprising:
forming a gate electrode, a gate pad and gate links on a substrate, the gate links having gate dummy patterns;
forming a gate insulating film on the gate electrode and the gate link;
forming a semiconductor layer on the gate insulating film;
forming a source electrode, a drain electrode, a data pad and data links on the semiconductor layer;
forming a protective film on the source and drain electrodes and the data link; and
forming a pixel electrode on the protective film,
wherein the gate dummy patterns are formed into the same vertical structure as any one of the gate links and the data links.

17. (Amended) A method of fabricating a liquid crystal display device, comprising:
forming a gate electrode, a gate pad and gate links on a substrate, the gate links having gate dummy patterns;
forming a gate insulating film a semiconductor layer on the gate electrode and the gate link;
forming a source electrode, a drain electrode, a data pad and data links on the semiconductor layer;
forming a protective film on the source and drain electrodes and the data link;
patterning the gate insulating film, the semiconductor layer, and the protective film, and
forming a pixel electrode on the protective film,
wherein the gate dummy patterns are formed into the same vertical structure as any one of the gate links and the data links.

Please add new claims 25-27 as follows.

--25. (New) The device of claim 5, wherein the data dummy patterns are formed into the same vertical structure as any one of the gate links and the data links.

26. (New) The method of claim 13, wherein the data dummy patterns are formed into

the same vertical structure as any one of the gate links and the data links.

27. (New) The method of claim 21, wherein the data dummy patterns are formed into the same vertical structure as any one of the gate links and the data links.--